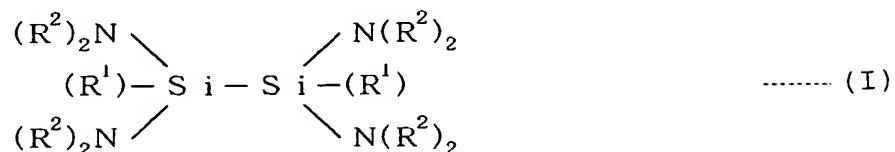


Abstract of the Disclosure

The method of forming a Si-containing thin film forms a film using an organic Si-containing compound having a Si-Si bond represented by the following formula (I):



wherein R¹ represents a hydrogen or a methyl group, and R² represents a methyl group, an ethyl group, a propyl group or a tertiary butyl group.